Lattice Semiconductor Corporation - LFE5U-45F-7BG256C Datasheet

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	11000
Number of Logic Elements/Cells	44000
Total RAM Bits	1990656
Number of I/O	197
Number of Gates	-
Voltage - Supply	1.045V ~ 1.155V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	256-LFBGA
Supplier Device Package	256-CABGA (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfe5u-45f-7bg256c

Figures

Tables

2. Architecture

2.1. Overview

Each ECP5/ECP5-5G device contains an array of logic blocks surrounded by Programmable I/O Cells (PIC). Interspersed between the rows of logic blocks are rows of sysMEM™ Embedded Block RAM (EBR) and rows of sysDSP™ Digital Signal Processing slices, as shown in Figure 2.1 on page 13. The LFE5-85 devices have three rows of DSP slices, the LFE5-45 devices have two rows, and both LFE5-25 and LFE5-12 devices have one. In addition, the LFE5UM/LFE5UM5G devices contain SERDES Duals on the bottom of the device.

The Programmable Functional Unit (PFU) contains the building blocks for logic, arithmetic, RAM and ROM functions. The PFU block is optimized for flexibility, allowing complex designs to be implemented quickly and efficiently. Logic Blocks are arranged in a two-dimensional array.

The ECP5/ECP5-5G devices contain one or more rows of sysMEM EBR blocks. sysMEM EBRs are large, dedicated 18 Kb fast memory blocks. Each sysMEM block can be configured in a variety of depths and widths as RAM or ROM. In addition, ECP5/ECP5-5G devices contain up to three rows of DSP slices. Each DSP slice has multipliers and adder/accumulators, which are the building blocks for complex signal processing capabilities.

The ECP5 devices feature up to four embedded 3.2 Gb/s SERDES channels, and the ECP5-5G devices feature up to four embedded 5 Gb/s SERDES channels. Each SERDES channel contains independent 8b/10b encoding / decoding, polarity adjust and elastic buffer logic. Each group of two SERDES channels, along with its Physical Coding Sublayer (PCS) block, creates a dual DCU (Dual Channel Unit). The functionality of the SERDES/PCS duals can be controlled by SRAM cell settings during device configuration or by registers that are addressable during device operation. The registers in every dual can be programmed via the SERDES Client Interface (SCI). These DCUs (up to two) are located at the bottom of the devices.

Each PIC block encompasses two PIOs (PIO pairs) with their respective sysI/O buffers. The sysI/O buffers of the ECP5/ECP5-5G devices are arranged in seven banks (eight banks for LFE5-85 devices in caBGA756 and caBGA554 packages), allowing the implementation of a wide variety of I/O standards. One of these banks (Bank 8) is shared with the programming interfaces. Half of the PIO pairs on the left and right edges of the device can be configured as LVDS transmit pairs, and all pairs on left and right can be configured as LVDS receive pairs. The PIC logic in the left and right banks also includes pre-engineered support to aid in the implementation of high speed source synchronous standards such as XGMII, 7:1 LVDS, along with memory interfaces including DDR3 and LPDDR3.

The ECP5/ECP5-5G registers in PFU and sysI/O can be configured to be SET or RESET. After power up and the device is configured, it enters into user mode with these registers SET/RESET according to the configuration setting, allowing the device entering to a known state for predictable system function.

Other blocks provided include PLLs, DLLs and configuration functions. The ECP5/ECP5-5G architecture provides up to four Delay-Locked Loops (DLLs) and up to four Phase-Locked Loops (PLLs). The PLL and DLL blocks are located at the corners of each device.

The configuration block that supports features such as configuration bit-stream decryption, transparent updates and dual-boot support is located at the bottom of each device, to the left of the SERDES blocks. Every device in the ECP5/ECP5-5G family supports a sysCONFIG™ ports located in that same corner, powered by Vccio8, allowing for serial or parallel device configuration.

In addition, every device in the family has a JTAG port. This family also provides an on-chip oscillator and soft error detect capability. The ECP5 devices use 1.1 V and ECP5UM5G devices use 1.2 V as their core voltage.

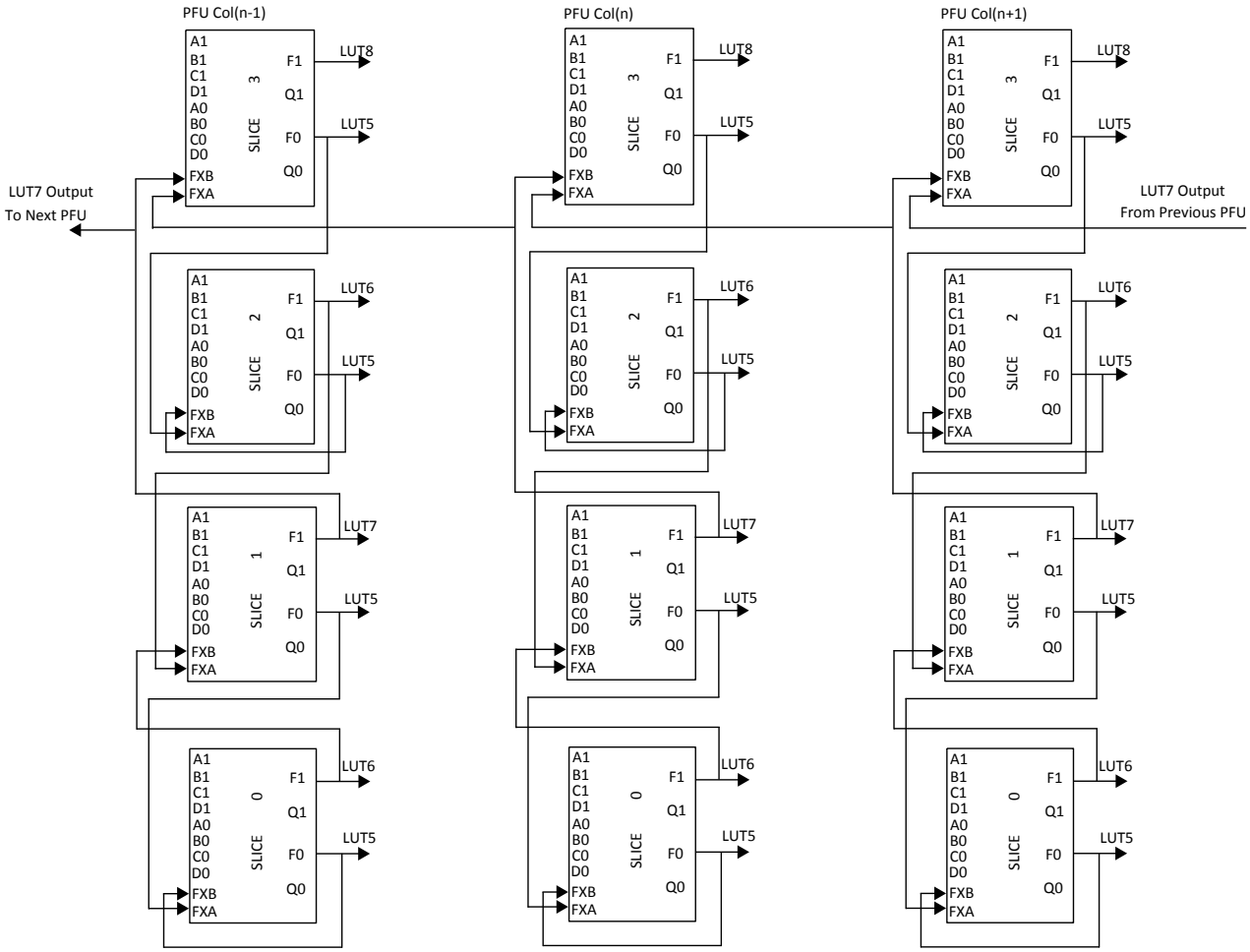


Figure 2.4. Connectivity Supporting LUT5, LUT6, LUT7, and LUT8

Table 2.2. Slice Signal Descriptions

Function	Type	Signal Names	Description
Input	Data signal	A0, B0, C0, D0	Inputs to LUT4
Input	Data signal	A1, B1, C1, D1	Inputs to LUT4
Input	Multi-purpose	M0	Multipurpose Input
Input	Multi-purpose	M1	Multipurpose Input
Input	Control signal	CE	Clock Enable
Input	Control signal	LSR	Local Set/Reset
Input	Control signal	CLK	System Clock
Input	Inter-PFU signal	FCI	Fast Carry-in[1]
Input	Inter-slice signal	FXA	Intermediate signal to generate LUT6, LUT7 and LUT8[2]
Input	Inter-slice signal	FXB	Intermediate signal to generate LUT6, LUT7 and LUT8[2]
Output	Data signals	F0, F1	LUT4 output register bypass signals
Output	Data signals	Q0, Q1	Register outputs
Output	Inter-PFU signal	FCO	Fast carry chain output[1]

Notes:

1. See Figure 2.3 on page 15 for connection details.
2. Requires two adjacent PFUs.

2.2.2. Modes of Operation

Slices 0-2 have up to four potential modes of operation: Logic, Ripple, RAM and ROM. Slice 3 is not needed for RAM mode, it can be used in Logic, Ripple, or ROM modes.

Logic Mode

In this mode, the LUTs in each slice are configured as 4-input combinatorial lookup tables. A LUT4 can have 16 possible input combinations. Any four input logic functions can be generated by programming this lookup table. Since there are two LUT4s per slice, a LUT5 can be constructed within one slice. Larger look-up tables such as LUT6, LUT7 and LUT8 can be constructed by concatenating other slices. Note that LUT8 requires more than four slices.

Ripple Mode

Ripple mode supports the efficient implementation of small arithmetic functions. In ripple mode, the following functions can be implemented by each slice:

- Addition 2-bit
- Subtraction 2-bit
- Add/Subtract 2-bit using dynamic control
- Up counter 2-bit
- Down counter 2-bit
- Up/Down counter with asynchronous clear
- Up/Down counter with preload (sync)
- Ripple mode multiplier building block
- Multiplier support
- Comparator functions of A and B inputs
  - A greater-than-or-equal-to B
  - A not-equal-to B
  - A less-than-or-equal-to B

Ripple Mode includes an optional configuration that performs arithmetic using fast carry chain methods. In this configuration (also referred to as CCU2 mode) two additional signals, Carry Generate and Carry Propagate, are generated on a per slice basis to allow fast arithmetic functions to be constructed by concatenating Slices.

RAM Mode

In this mode, a 16x4-bit distributed single port RAM (SPR) can be constructed in one PFU using each LUT block in Slice 0 and Slice 1 as a 16 x 2-bit memory in each slice. Slice 2 is used to provide memory address and control signals.
A 16 x 2-bit pseudo dual port RAM (PDPR) memory is created in one PFU by using one Slice as the read-write port and the other companion slice as the read-only port. The slice with the read-write port updates the SRAM data contents in both slices at the same write cycle.

ECP5/ECP5-5G devices support distributed memory initialization.

The Lattice design tools support the creation of a variety of different size memories. Where appropriate, the software will construct these using distributed memory primitives that represent the capabilities of the PFU. Table 2.3 lists the number of slices required to implement different distributed RAM primitives. For more information about using RAM in ECP5/ECP5-5G devices, refer to ECP5 and ECP5-5G Memory Usage Guide (TN1264).

Table 2.3. Number of Slices Required to Implement Distributed RAM

	SPR 16 X 4	PDPR 16 X 4
Number of slices	3	6

Note: SPR = Single Port RAM, PDPR = Pseudo Dual Port RAM

ROM Mode

ROM mode uses the LUT logic; hence, Slices 0 through 3 can be used in ROM mode. Preloading is accomplished through the programming interface during PFU configuration.

For more information, refer to ECP5 and ECP5-5G Memory Usage Guide (TN1264).

2.3. Routing

There are many resources provided in the ECP5/ECP5-5G devices to route signals individually or as busses with related control signals. The routing resources consist of switching circuitry, buffers and metal interconnect (routing) segments.

The ECP5/ECP5-5G family has an enhanced routing architecture that produces a compact design. The Diamond design software tool suites take the output of the synthesis tool and places and routes the design.

2.4. Clocking Structure

ECP5/ECP5-5G clocking structure consists of clock synthesis blocks (sysCLOCK PLL); balanced clock tree networks (PCLK and ECLK trees); and efficient clock logic modules (CLOCK DIVIDER and Dynamic Clock Select (DCS), Dynamic Clock Control (DCC) and DLL). All of these functions are described below.

2.4.1. sysCLOCK PLL

The sysCLOCK PLLs provide the ability to synthesize clock frequencies. The devices in the ECP5/ECP5-5G family support two to four full-featured General Purpose PLLs. The sysCLOCK PLLs provide the ability to synthesize clock frequencies.

The architecture of the PLL is shown in Figure 2.5. A description of the PLL functionality follows.

CLKI is the reference frequency input to the PLL and its source can come from two different external CLK inputs or from internal routing. A non-glitchless 2-to-1 input multiplexor is provided to dynamically select between two different external reference clock sources. The CLKI input feeds into the input Clock Divider block.

CLKFB is the feedback signal to the PLL which can come from internal feedback path, routing or an external I/O pin. The feedback divider is used to multiply the reference frequency and thus synthesize a higher frequency clock output.

The PLL has four clock outputs CLKOP, CLKOS, CLKOS2 and CLKOS3. Each output has its own output divider, thus allowing the PLL to generate different frequencies for each output. The output dividers can have a value from 1 to 128. The CLKOP, CLKOS, CLKOS2, and CLKOS3 outputs can all be used to drive the primary clock network. Only CLKOP and CLKOS outputs can go to the edge clock network.

The setup and hold times of the device can be improved by programming a phase shift into the CLKOS, CLKOS2, and CLKOS3 output clocks which will advance or delay the output clock with reference to the CLKOP output clock. This phase shift can be either programmed during configuration or can be adjusted dynamically using the PHASESEL, PHASEDIR, PHASESTEP, and PHASELOADREG ports.

The LOCK signal is asserted when the PLL determines it has achieved lock and de-asserted if a loss of lock is detected.

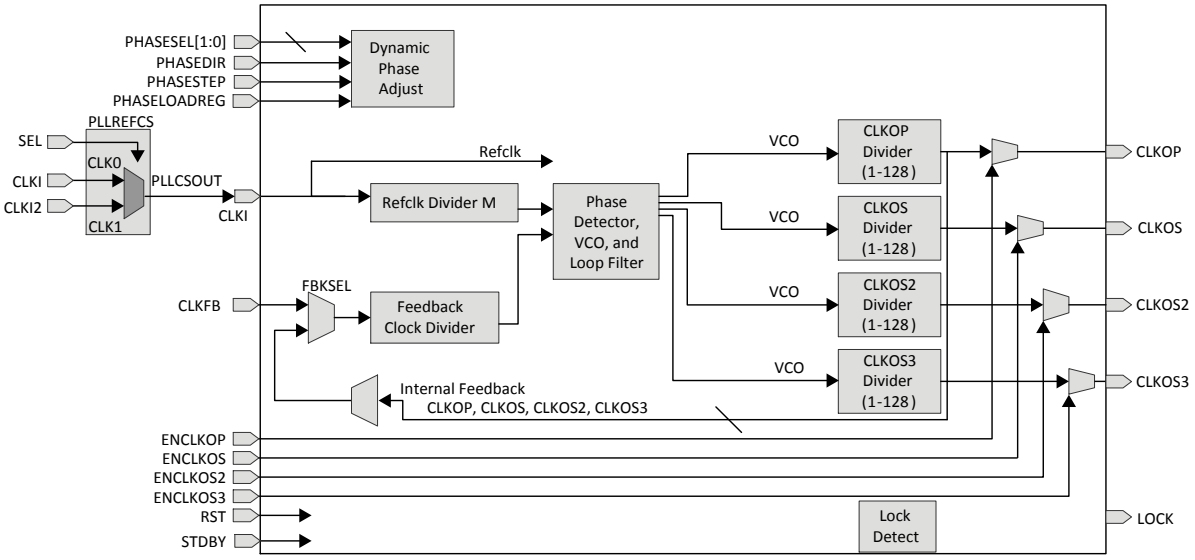


Figure 2.5. General Purpose PLL Diagram

3.7. Hot Socketing Requirements

Table 3.6. Hot Socketing Requirements

Description	Min	Typ	Max	Unit
Input current per SERDES I/O pin when device is powered down and inputs driven.	—	—	8	mA
Input current per HDIN pin when device power supply is off, inputs driven[1, 2]	—	—	15	mA
Current per HDIN pin when device power ramps up, input driven[3]	—	—	50	mA
Current per HDOUT pin when device power supply is off, outputs pulled up[4]	—	—	30	mA

Notes:

1. Device is powered down with all supplies grounded, both HDINP and HDINN inputs driven by a CML driver with maximum allowed output V_{CCHTX}, 8b/10b data, no external AC coupling.
2. Each P and N input must have less than the specified maximum input current during hot plug. For a device with 2 DCU, the total input current would be 15 mA * 4 channels * 2 input pins per channel = 120 mA.
3. Device power supplies are ramping up (V_{CCA} and V_{CCAUX}), both HDINP and HDINN inputs are driven by a CML driver with maximum allowed output V_{CCHTX}, 8b/10b data, internal AC coupling.
4. Device is powered down with all supplies grounded. Both HDOUTP and HDOUN outputs are pulled up to V_{CCHTX} by the far end receiver termination of 50 Ω single ended.

3.8. ESD Performance

Refer to the ECP5 and ECP5-5G Product Family Qualification Summary for complete qualification data, including ESD performance.

3.9. DC Electrical Characteristics

Over Recommended Operating Conditions

Table 3.7. DC Electrical Characteristics

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{IL}, I_{IH}[1, 4]	Input or I/O Low Leakage	$0 \le V_{IN} \le V_{CCIO}$	—	—	10	µA
I_{IH}[1, 3]	Input or I/O High Leakage	$V_{CCIO} < V_{IN} \le V_{IH(MAX)}$	—	—	100	µA
I_{PU}	I/O Active Pull-up Current, sustaining logic HIGH state	$0.7\ V_{CCIO} \le V_{IN} \le V_{CCIO}$	–30	—	—	µA
	I/O Active Pull-up Current, pulling down from logic HIGH state	$0 \le V_{IN} \le 0.7\ V_{CCIO}$	—	—	–150	µA
I_{PD}	I/O Active Pull-down Current, sustaining logic LOW state	$0 \le V_{IN} \le V_{IL}$ (MAX)	30	—	—	µA
	I/O Active Pull-down Current, pulling up from logic LOW state	$0 \le V_{IN} \le V_{CCIO}$	—	—	150	µA
C1	I/O Capacitance[2]	V_{CCIO} = 3.3 V, 2.5 V, 1.8 V, 1.5 V, 1.2 V, V_{CC} = 1.2 V, V_{IO} = 0 to $V_{IH(MAX)}$	—	5	8	pf
C2	Dedicated Input Capacitance[2]	V_{CCIO} = 3.3 V, 2.5 V, 1.8 V, 1.5 V, 1.2 V, V_{CC} = 1.2 V, V_{IO} = 0 to $V_{IH(MAX)}$	—	5	7	pf
V_{HYST}	Hysteresis for Single-Ended Inputs	V_{CCIO} = 3.3 V	—	300	—	mV
		V_{CCIO} = 2.5 V	—	250	—	mV

Notes:

1. Input or I/O leakage current is measured with the pin configured as an input or as an I/O with the output driver tristated. It is not measured with the output driver active. Bus maintenance circuits are disabled.
2. T_A 25 °C, f = 1.0 MHz.
3. Applicable to general purpose I/Os in top and bottom banks.
4. When used as V_{REF}, maximum leakage= 25 µA.

3.12. sysI/O Recommended Operating Conditions

Table 3.11. sysI/O Recommended Operating Conditions

Standard	V_{CCIO}			V_{REF} (V)		
	Min	Typ	Max	Min	Typ	Max
LVCMOS33[1]	3.135	3.3	3.465	—	—	—
LVCMOS33D[3] Output	3.135	3.3	3.465	—	—	—
LVCMOS25[1]	2.375	2.5	2.625	—	—	—
LVCMOS18	1.71	1.8	1.89	—	—	—
LVCMOS15	1.425	1.5	1.575	—	—	—
LVCMOS12[1]	1.14	1.2	1.26	—	—	—
LVTTL33[1]	3.135	3.3	3.465	—	—	—
SSTL15_I, _II[2]	1.43	1.5	1.57	0.68	0.75	0.9
SSTL18_I, _II[2]	1.71	1.8	1.89	0.833	0.9	0.969
SSTL135_I, _II[2]	1.28	1.35	1.42	0.6	0.675	0.75
HSUL12[2]	1.14	1.2	1.26	0.588	0.6	0.612
MIPI D-PHY LP Input[3, 5]	1.425	1.5	1.575	—	—	—
LVDS25[1, 3] Output	2.375	2.5	2.625	—	—	—
subLVS[3] (Input only)	—	—	—	—	—	—
SLVS[3] (Input only)	—	—	—	—	—	—
LVDS25E[3] Output	2.375	2.5	2.625	—	—	—
MLVDS[3] Output	2.375	2.5	2.625	—	—	—
LVPECL33[1, 3] Output	3.135	3.3	3.465	—	—	—
BLVDS25[1, 3] Output	2.375	2.5	2.625	—	—	—
HSULD12D[2, 3]	1.14	1.2	1.26	—	—	—
SSTL135D_I, II[2, 3]	1.28	1.35	1.42	—	—	—
SSTL15D_I, II[2, 3]	1.43	1.5	1.57	—	—	—
SSTL18D_I[1, 2, 3], II[1, 2, 3]	1.71	1.8	1.89	—	—	—

Notes:

1. For input voltage compatibility, refer to ECP5 and ECP5-5G sysIO Usage Guide (TN1262).
2. V_{REF} is required when using Differential SSTL and HSUL to interface to DDR/LPDDR memories.
3. These differential inputs use LVDS input comparator, which uses V_{CCAUX} power
4. All differential inputs and LVDS25 output are supported in the Left and Right banks only. Refer to ECP5 and ECP5-5G sysIO Usage Guide (TN1262) for details.
5. MIPI D-PHY LP input can be implemented by powering VCCIO to 1.5V, and select MIPI LP primitive to meet MIPI Alliance spec on V_{IH} and V_{IL}. It can also be implemented as LVCMOS12 with VCCIO at 1.2V, which would meet V_{IH}/V_{IL} spec on LVCOM12.

3.14.4. LVDS25E

The top and bottom sides of ECP5/ECP5-5G devices support LVDS outputs via emulated complementary LVCMOS outputs in conjunction with a parallel resistor across the driver outputs. The scheme shown in Figure 3.1 is one possible solution for point-to-point signals.

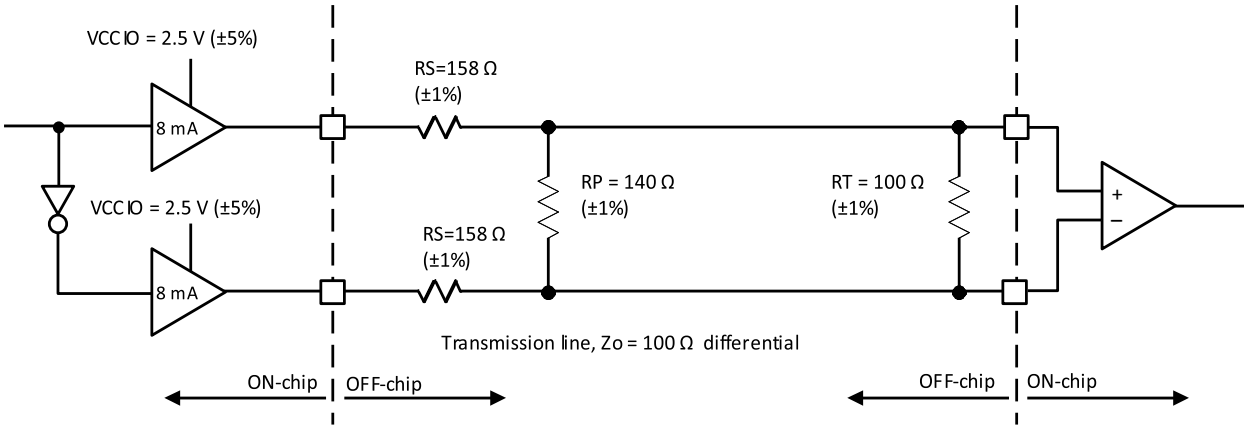


Figure 3.1. LVDS25E Output Termination Example

Table 3.14. LVDS25E DC Conditions

Parameter	Description	Typical	Unit
V_{CCIO}	Output Driver Supply (±5%)	2.50	V
Z_{OUT}	Driver Impedance	20	Ω
R_S	Driver Series Resistor (±1%)	158	Ω
R_P	Driver Parallel Resistor (±1%)	140	Ω
R_T	Receiver Termination (±1%)	100	Ω
V_{OH}	Output High Voltage	1.43	V
V_{OL}	Output Low Voltage	1.07	V
V_{OD}	Output Differential Voltage	0.35	V
V_{CM}	Output Common Mode Voltage	1.25	V
Z_{BACK}	Back Impedance	100.5	Ω
I_{DC}	DC Output Current	6.03	mA

Note: For input buffer, see LVDS Table 3.13 on page 55.

3.14.8. SLVS

Scalable Low-Voltage Signaling (SLVS) is based on a point-to-point signaling method defined in the JEDEC JESD8-13 (SLVS-400) standard. This standard evolved from the traditional LVDS standard and relies on the advantage of its use of smaller voltage swings and a lower common-mode voltage. The 200 mV (400 mV p-p) SLVS swing contributes to a reduction in power.

The ECP5/ECP5-5G devices can receive differential input up to 800 Mb/s with its LVDS input buffer. This LVDS input buffer is used to meet the SLVS input standard specified by the JEDEC standard. The SLVS output parameters are compared to ECP5/ECP5-5G LVDS input parameters, as listed in Table 3.18.

Table 3.18. Input to SLVS

Parameter	ECP5/ECP5-5G LVDS Input	SLVS Output	Unit
Vcm (min)	50	150	mV
Vcm (max)	2350	250	mV
Differential Voltage (min)	100	140	mV
Differential Voltage (max)	—	270	mV

ECP5/ECP5-5G does not support SLVS output. However, SLVS output can be created using ECP5/ECP5-5G LVDS outputs by level shift to meet the low Vcm/Vod levels required by SLVS. Figure 3.5 shows how the LVDS output can be shifted external to meet SLVS levels.

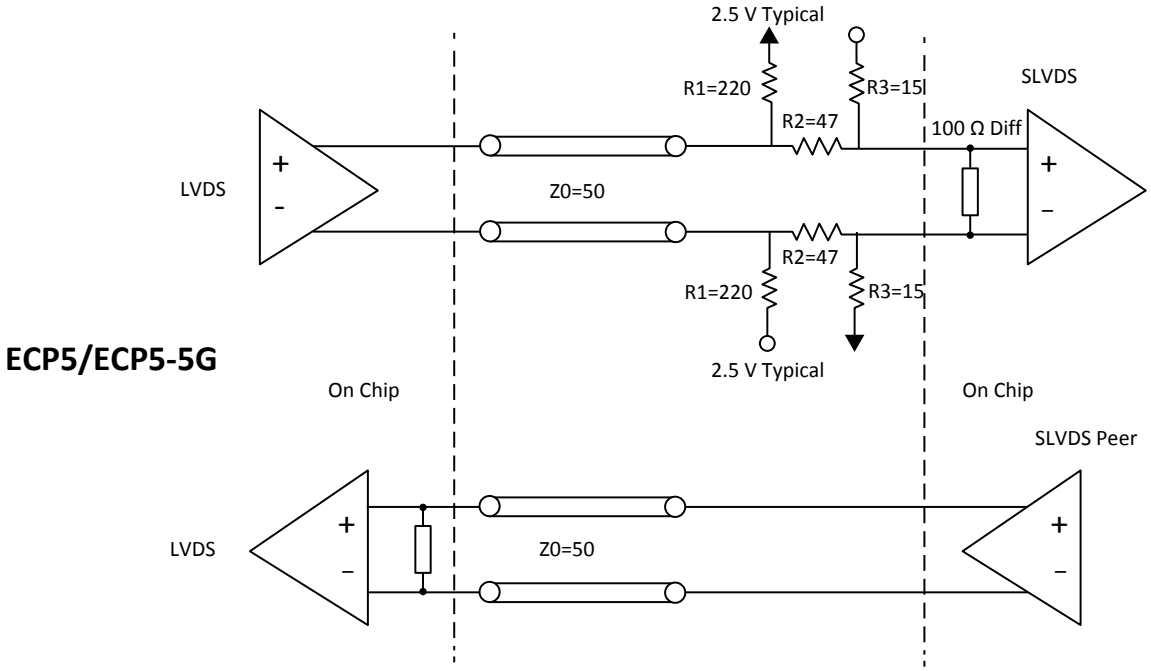


Figure 3.5. SLVS Interface

Table 3.22. ECP5/ECP5-5G External Switching Characteristics *(Continued)*

Parameter	Description	Device	–8		–7		–6		Unit
			Min	Max	Min	Max	Min	Max	
t_{H_DELPLL}	Clock to Data Hold - PIO Input Register with Data Input Delay	All Devices	0	—	0	—	0	—	ns
Generic DDR Input									
Generic DDRX1 Inputs With Clock and Data Centered at Pin (GDDRX1_RX.SCLK.Centered) Using PCLK Clock Input - Figure 3.6									
$t_{SU\_GDDRX1\_centered}$	Data Setup Before CLK Input	All Devices	0.52	—	0.52	—	0.52	—	ns
$t_{HD\_GDDRX1\_centered}$	Data Hold After CLK Input	All Devices	0.52	—	0.52	—	0.52	—	ns
$f_{DATA\_GDDRX1\_centered}$	GDDRX1 Data Rate	All Devices	—	500	—	500	—	500	Mb/s
$f_{MAX\_GDDRX1\_centered}$	GDDRX1 CLK Frequency (SCLK)	All Devices	—	250	—	250	—	250	MHz
Generic DDRX1 Inputs With Clock and Data Aligned at Pin (GDDRX1_RX.SCLK.Aligned) Using PCLK Clock Input - Figure 3.7									
$t_{SU\_GDDRX1\_aligned}$	Data Setup from CLK Input	All Devices	—	–0.55	—	–0.55	—	–0.55	ns + 1/2 UI
$t_{HD\_GDDRX1\_aligned}$	Data Hold from CLK Input	All Devices	0.55	—	0.55	—	0.55	—	ns + 1/2 UI
$f_{DATA\_GDDRX1\_aligned}$	GDDRX1 Data Rate	All Devices	—	500	—	500	—	500	Mb/s
$f_{MAX\_GDDRX1\_aligned}$	GDDRX1 CLK Frequency (SCLK)	All Devices	—	250	—	250	—	250	MHz
Generic DDRX2 Inputs With Clock and Data Centered at Pin (GDDRX2_RX.ECLK.Centered) Using PCLK Clock Input, Left and Right sides Only - Figure 3.6									
$t_{SU\_GDDRX2\_centered}$	Data Setup before CLK Input	All Devices	0.321	—	0.403	—	0.471	—	ns
$t_{HD\_GDDRX2\_centered}$	Data Hold after CLK Input	All Devices	0.321	—	0.403	—	0.471	—	ns
$f_{DATA\_GDDRX2\_centered}$	GDDRX2 Data Rate	All Devices	—	800	—	700	—	624	Mb/s
$f_{MAX\_GDDRX2\_centered}$	GDDRX2 CLK Frequency (ECLK)	All Devices	—	400	—	350	—	312	MHz
Generic DDRX2 Inputs With Clock and Data Aligned at Pin (GDDRX2_RX.ECLK.Aligned) Using PCLK Clock Input, Left and Right sides Only - Figure 3.7									
$t_{SU\_GDDRX2\_aligned}$	Data Setup from CLK Input	All Devices	—	–0.344	—	–0.42	—	-0.495	ns + 1/2 UI
$t_{HD\_GDDRX2\_aligned}$	Data Hold from CLK Input	All Devices	0.344	—	0.42	—	0.495	—	ns + 1/2 UI
$f_{DATA\_GDDRX2\_aligned}$	GDDRX2 Data Rate	All Devices	—	800	—	700	—	624	Mb/s
$f_{MAX\_GDDRX2\_aligned}$	GDDRX2 CLK Frequency	All Devices	—	400	—	350	—	312	MHz
Video DDRX71 Inputs With Clock and Data Aligned at Pin (GDDRX71_RX.ECLK) Using PLL Clock Input, Left and Right sides Only Figure 3.11									
$t_{SU\_LVDS71\_i}$	Data Setup from CLK Input (bit i)	All Devices	—	–0.271	—	–0.39	—	–0.41	ns+(1/2+i) * UI
$t_{HD\_LVDS71\_i}$	Data Hold from CLK Input (bit i)	All Devices	0.271	—	0.39	—	0.41	—	ns+(1/2+i) * UI
f_{DATA_LVDS71}	DDR71 Data Rate	All Devices	—	756	—	620	—	525	Mb/s
f_{MAX_LVDS71}	DDR71 CLK Frequency (ECLK)	All Devices	—	378	—	310	—	262.5	MHz

Table 3.22. ECP5/ECP5-5G External Switching Characteristics *(Continued)*

Parameter	Description	Device	–8		–7		–6		Unit
			Min	Max	Min	Max	Min	Max	
Generic DDR Output									
Generic DDRX1 Outputs With Clock and Data Centered at Pin (GDDRX1_TX.SCLK.Centered) Using PCLK Clock Input - Figure 3.6									
$t_{DVB\_GDDRX1\_centered}$	Data Output Valid before CLK Output	All Devices	–0.67	—	–0.67	—	–0.67	—	ns + 1/2 UI
$t_{DVA\_GDDRX1\_centered}$	Data Output Valid after CLK Output	All Devices	–0.67	—	–0.67	—	–0.67	—	ns + 1/2 UI
$f_{DATA\_GDDRX1\_centered}$	GDDRX1 Data Rate	All Devices	—	500	—	500	—	500	Mb/s
$f_{MAX\_GDDRX1\_centered}$	GDDRX1 CLK Frequency (SCLK)	All Devices	—	250	—	250	—	250	MHz
Generic DDRX1 Outputs With Clock and Data Aligned at Pin (GDDRX1_TX.SCLK.Aligned) Using PCLK Clock Input - Figure 3.9									
$t_{DIB\_GDDRX1\_aligned}$	Data Output Invalid before CLK Output	All Devices	–0.3	—	–0.3	—	–0.3	—	ns
$t_{DIA\_GDDRX1\_aligned}$	Data Output Invalid after CLK Output	All Devices	—	0.3	—	0.3	—	0.3	ns
$f_{DATA\_GDDRX1\_aligned}$	GDDRX1 Data Rate	All Devices	—	500	—	500	—	500	Mb/s
$f_{MAX\_GDDRX1\_aligned}$	GDDRX1 CLK Frequency (SCLK)	All Devices	—	250	—	250	—	250	MHz
Generic DDRX2 Outputs With Clock and Data Centered at Pin (GDDRX2_TX.ECLK.Centered) Using PCLK Clock Input, Left and Right sides Only - Figure 3.8									
$t_{DVB\_GDDRX2\_centered}$	Data Output Valid Before CLK Output	All Devices	–0.442	—	–0.56	—	–0.676	—	ns + 1/2 UI
$t_{DVA\_GDDRX2\_centered}$	Data Output Valid After CLK Output	All Devices	—	0.442	—	0.56	—	0.676	ns + 1/2 UI
$f_{DATA\_GDDRX2\_centered}$	GDDRX2 Data Rate	All Devices	—	800	—	700	—	624	Mb/s
$f_{MAX\_GDDRX2\_centered}$	GDDRX2 CLK Frequency (ECLK)	All Devices	—	400	—	350	—	312	MHz
Generic DDRX2 Outputs With Clock and Data Aligned at Pin (GDDRX2_TX.ECLK.Aligned) Using PCLK Clock Input, Left and Right sides Only - Figure 3.9									
$t_{DIB\_GDDRX2\_aligned}$	Data Output Invalid before CLK Output	All Devices	–0.16	—	–0.18	—	–0.2	—	ns
$t_{DIA\_GDDRX2\_aligned}$	Data Output Invalid after CLK Output	All Devices	—	0.16	—	0.18	—	0.2	ns
$f_{DATA\_GDDRX2\_aligned}$	GDDRX2 Data Rate	All Devices	—	800	—	700	—	624	Mb/s
$f_{MAX\_GDDRX2\_aligned}$	GDDRX2 CLK Frequency (ECLK)	All Devices	—	400	—	350	—	312	MHz
Video DDRX71 Outputs With Clock and Data Aligned at Pin (GDDRX71_TX.ECLK) Using PLL Clock Input, Left and Right sides Only - Figure 3.12									
$t_{DIB\_LVDS71\_i}$	Data Output Invalid before CLK Output	All Devices	–0.16	—	–0.18	—	–0.2	—	ns + (i) * UI
$t_{DIA\_LVDS71\_i}$	Data Output Invalid after CLK Output	All Devices	—	0.16	—	0.18	—	0.2	ns + (i) * UI
f_{DATA_LVDS71}	DDR71 Data Rate	All Devices	—	756	—	620	—	525	Mb/s
f_{MAX_LVDS71}	DDR71 CLK Frequency (ECLK)	All Devices	—	378	—	310	—	262.5	MHz
Memory Interface									
DDR2/DDR3/DDR3L/LPDDR2/LPDDR3 READ (DQ Input Data are Aligned to DQS)									
t_{DVBDQ_DDR2} t_{DVBDQ_DDR3} t_{DVBDQ_DDR3L} t_{DVBDQ_LPDDR2} t_{DVBDQ_LPDDR3}	Data Output Valid before DQS Input	All Devices	—	–0.26	—	–0.317	—	–0.374	ns + 1/2 UI
t_{DVADQ_DDR2} t_{DVADQ_DDR3} t_{DVADQ_DDR3L} t_{DVADQ_LPDDR2} t_{DVADQ_LPDDR3}	Data Output Valid after DQS Input	All Devices	0.26	—	0.317	—	0.374	—	ns + 1/2 UI

Table 3.22. ECP5/ECP5-5G External Switching Characteristics *(Continued)*

Parameter	Description	Device	–8		–7		–6		Unit
			Min	Max	Min	Max	Min	Max	
f_{DATA_DDR2} f_{DATA_DDR3} f_{DATA_DDR3L} f_{DATA_LPDDR2} f_{DATA_LPDDR3}	DDR Memory Data Rate	All Devices	—	800	—	700	—	624	Mb/s
f_{MAX_DDR2} f_{MAX_DDR3} f_{MAX_DDR3L} f_{MAX_LPDDR2} f_{MAX_LPDDR3}	DDR Memory CLK Frequency (ECLK)	All Devices	—	400	—	350	—	312	MHz
DDR2/DDR3/DDR3L/LPDDR2/LPDDR3 WRITE (DQ Output Data are Centered to DQS)									
t_{DQVBS_DDR2} t_{DQVBS_DDR3} t_{DQVBS_DDR3L} t_{DQVBS_LPDDR2} t_{DQVBS_LPDDR3}	Data Output Valid before DQS Output	All Devices	—	–0.25	—	–0.25	—	-0.25	UI
t_{DQVAS_DDR2} t_{DQVAS_DDR3} t_{DQVAS_DDR3L} t_{DQVAS_LPDDR2} t_{DQVAS_LPDDR3}	Data Output Valid after DQS Output	All Devices	0.25	—	0.25	—	0.25	—	UI
f_{DATA_DDR2} f_{DATA_DDR3} f_{DATA_DDR3L} f_{DATA_LPDDR2} f_{DATA_LPDDR3}	DDR Memory Data Rate	All Devices	—	800	—	700	—	624	Mb/s
f_{MAX_DDR2} f_{MAX_DDR3} f_{MAX_DDR3L} f_{MAX_LPDDR2} f_{MAX_LPDDR3}	DDR Memory CLK Frequency (ECLK)	All Devices	—	400	—	350	—	312	MHz

Notes:

1. Commercial timing numbers are shown. Industrial numbers are typically slower and can be extracted from the Diamond software.
2. General I/O timing numbers are based on LVCMOS 2.5, 12 mA, Fast Slew Rate, 0pf load.
   Generic DDR timing are numbers based on LVDS I/O.
   DDR2 timing numbers are based on SSTL18.
   DDR3 timing numbers are based on SSTL15.
   LPDDR2 and LPDDR3 timing numbers are based on HSUL12.
3. Uses LVDS I/O standard for measurements.
4. Maximum clock frequencies are tested under best case conditions. System performance may vary upon the user environment.
5. All numbers are generated with the Diamond software.

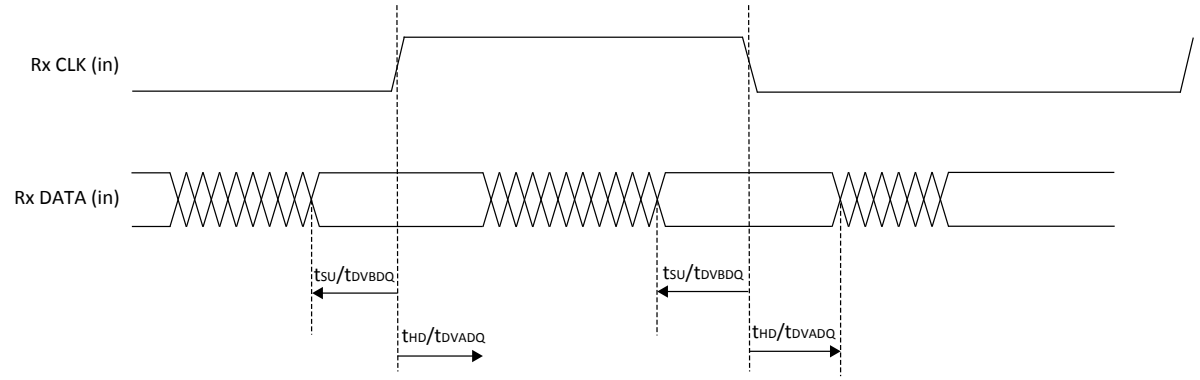


Figure 3.6. Receiver RX.CLK.Centered Waveforms

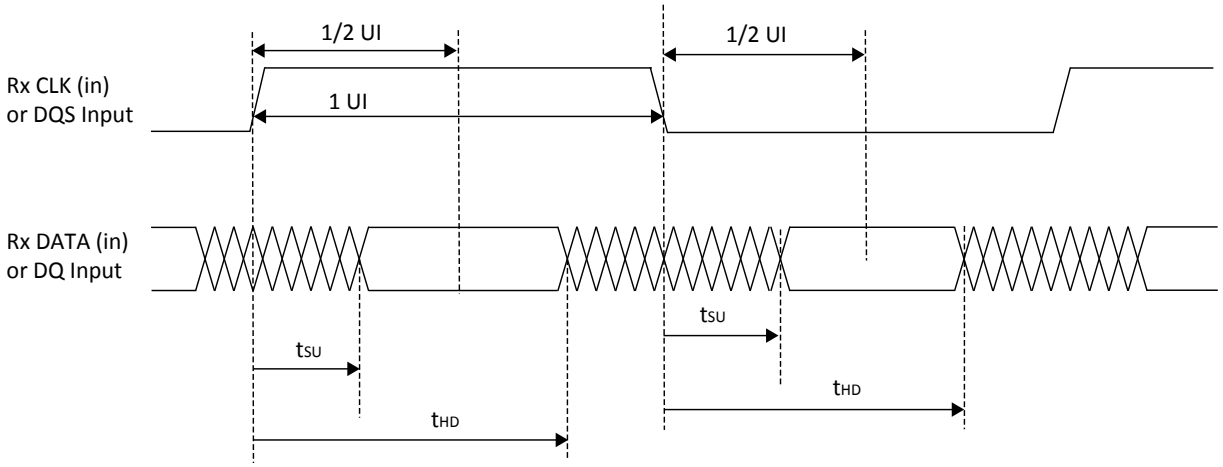


Figure 3.7. Receiver RX.CLK.Aligned and DDR Memory Input Waveforms

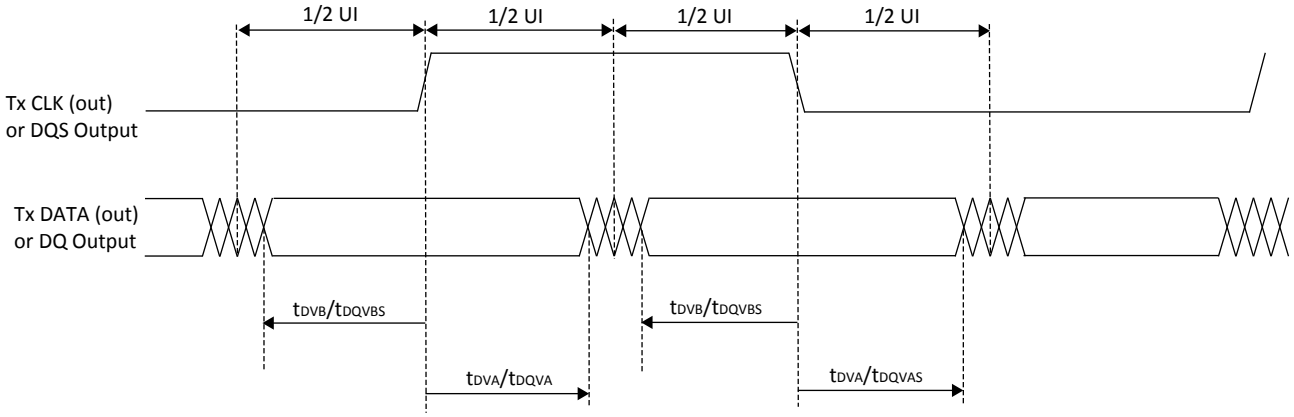


Figure 3.8. Transmit TX.CLK.Centered and DDR Memory Output Waveforms

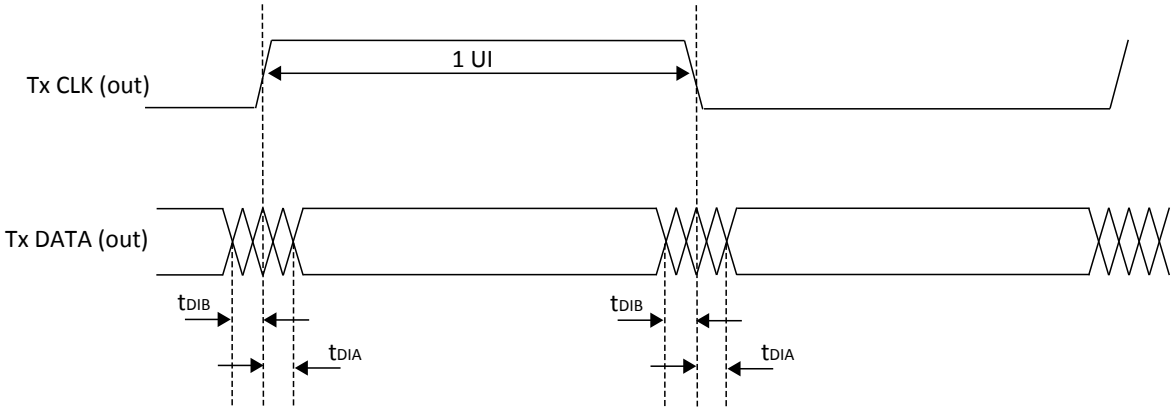
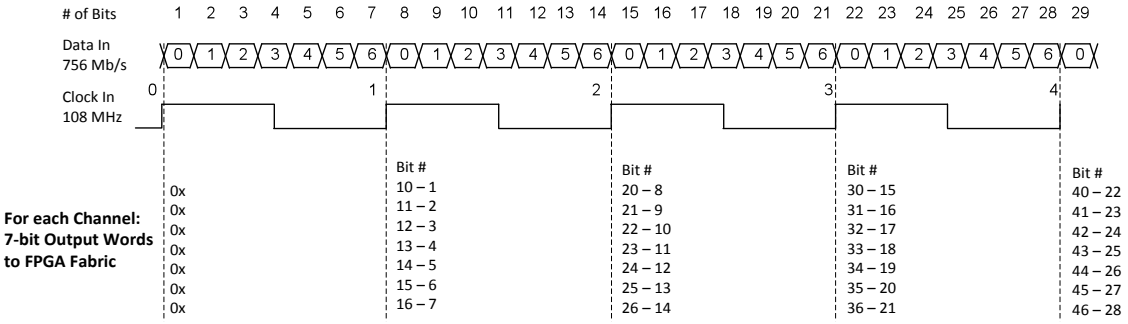


Figure 3.9. Transmit TX.CLK.Aligned Waveforms

Receiver – Shown for one LVDS Channel



Transmitter – Shown for one LVDS Channel

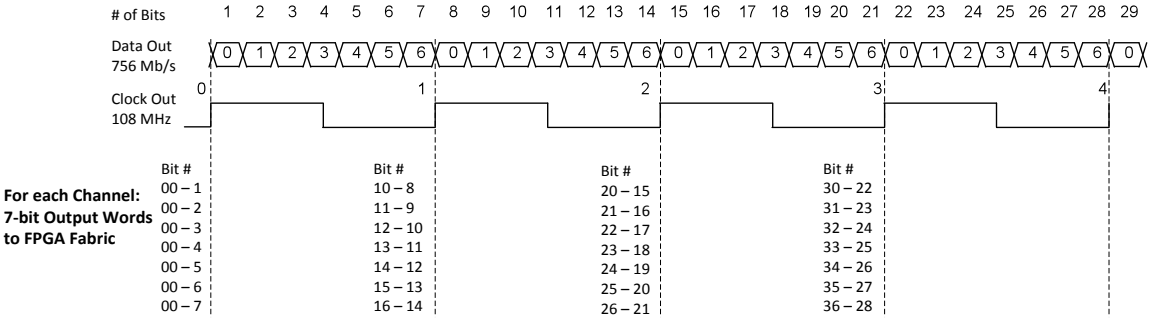


Figure 3.10. DDRX71 Video Timing Waveforms

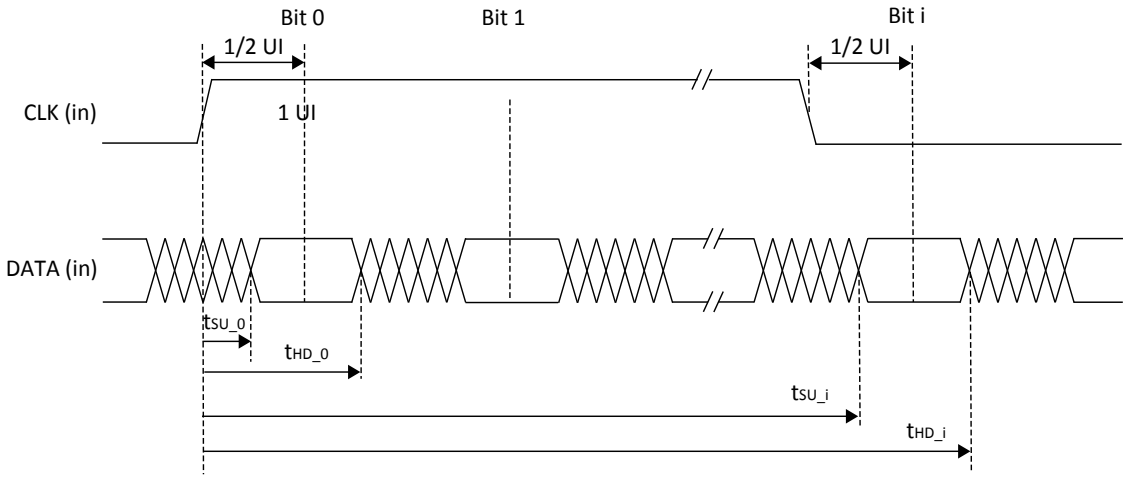


Figure 3.11. Receiver DDRX71_RX Waveforms

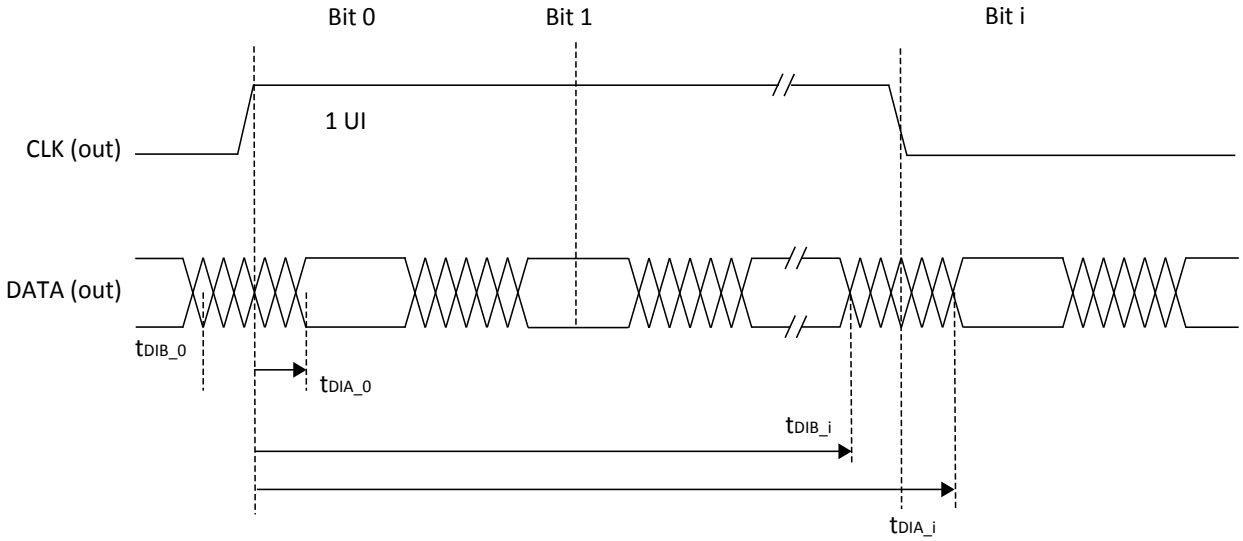


Figure 3.12. Transmitter DDRX71_TX Waveforms

3.26. CPRI LV2 E.48 Electrical and Timing Characteristics – Preliminary

Table 3.32. CPRI LV2 E.48 Electrical and Timing Characteristics

Symbol	Description	Test Conditions	Min	Typ	Max	Unit
Transmit						
UI	Unit Interval	—	203.43	203.45	203.47	ps
T_{DCD}	Duty Cycle Distortion	—	—	—	0.05	UI
J_{UBHPJ}	Uncorrelated Bounded High Probability Jitter	—	—	—	0.15	UI
J_{TOTAL}	Total Jitter	—	—	—	0.3	UI
$Z_{RX-DIFF-DC}$	DC differential Impedance	—	80	—	120	Ω
T_{SKEW}	Skew between differential signals	—	—	—	9	ps
$R_{LTX-DIFF}$	Tx Differential Return Loss (S22), including package and silicon	100 MHz < freq < 3.6864 GHz	—	—	–8	dB
		3.6864 GHz < freq < 4.9152 GHz	—	—	–8 + 16.6 *log (freq/3.6864)	dB
R_{LTX-CM}	Tx Common Mode Return Loss, including package and silicon	100 MHz < freq < 3.6864 GHz	6	—	—	dB
$I_{TX-SHORT}$	Transmitter short-circuit current	—	—	—	100	mA
$T_{RISE\_FALL-DIFF}$	Differential Rise and Fall Time	—		—	—	ps
$L_{TX-SKEW}$	Lane-to-lane output skew	—	—	—		ps
Receive						
UI	Unit Interval	—	203.43	203.45	203.47	ps
$V_{RX-DIFF-PP}$	Differential Rx peak-peak voltage	—	—	—	1.2	V, p-p
$V_{RX-EYE\_Y1\_Y2}$	Receiver eye opening mask, Y1 and Y2	—	62.5	—	375	mV, diff
V_{RX-EYE_X1}	Receiver eye opening mask, X1	—	—	—	0.3	UI
T_{RX-TJ}	Receiver total jitter tolerance (not including sinusoidal)	—	—	—	0.6	UI
$R_{LRX-DIFF}$	Receiver differential Return Loss, package plus silicon	100 MHz < freq < 3.6864 GHz	—	—	–8	dB
		3.6864 GHz < freq < 4.9152 GHz	—	—	–8 + 16.6 *log (freq/3.6864)	dB
R_{LRX-CM}	Receiver common mode Return Loss, package plus silicon	—	6	—	—	dB
$Z_{RX-DIFF-DC}$	Receiver DC differential impedance	—	80	100	120	Ω

Note: Data is measured with PRBS7 data pattern, not with PRBS-31 pattern.

Pin Information Summary		LFE5UM/ LFE5UM5G-25		LFE5UM/LFE5UM5G-45			LFE5UM/LFE5UM5G-85			
Pin Type		285 csfBG	381 caBGA	285 csfBGA	381 caBG	554 caBGA	285 csfBGA	381 caBG	554 caBGA	756 caBGA
TAP		4	4	4	4	4	4	4	4	4
Miscellaneous Dedicated Pins		7	7	7	7	7	7	7	7	7
GND		83	59	83	59	113	83	59	113	166
NC		1	8	1	2	33	1	0	17	29
Reserved		0	2	0	2	4	0	2	4	4
SERDES		14	28	14	28	28	14	28	28	28
VCCA (SERDES)	VCCA0	2	2	2	2	6	2	2	6	8
	VCCA1	0	2	0	2	6	0	2	6	9
VCCAUX (SERDES)	VCCAUXA0	2	2	2	2	2	2	2	2	2
	VCCAUXA1	0	2	0	2	2	0	2	2	2
GNDA (SERDES)		26	26	26	26	49	26	26	49	60
Total Balls		285	381	285	381	554	285	381	554	756
High Speed Differential Input / Output Pairs	Bank 0	0	0	0	0	0	0	0	0	0
	Bank 1	0	0	0	0	0	0	0	0	0
	Bank 2	10/8	16/8	10/8	16/8	16/8	10/8	17/9	16/8	24/12
	Bank 3	14/7	16/8	14/7	16/8	24/12	14/7	16/8	24/12	32/16
	Bank 4	0	0	0	0	0	0	0	0	0
	Bank 6	13/6	16/8	13/6	16/8	24/12	13/6	16/8	24/12	32/16
	Bank 7	8/6	16/8	8/6	16/8	16/8	8/6	16/8	16/8	24/12
	Bank 8	0	0	0	0	0	0	0	0	0
Total High Speed Differential I/O Pairs		45/2	64/32	45/27	64/3	80/40	45/27	65/3	80/40	112/5
DQS Groups (> 11 pins in group)	Bank 0	0	0	0	0	0	0	0	0	0
	Bank 1	0	0	0	0	0	0	0	0	0
	Bank 2	1	2	1	2	2	1	2	2	3
	Bank 3	2	2	2	2	3	2	2	3	4
	Bank 4	0	0	0	0	0	0	0	0	0
	Bank 6	2	2	2	2	3	2	2	3	4
	Bank 7	1	2	1	2	2	1	2	2	3
	Bank 8	0	0	0	0	0	0	0	0	0
Total DQS Groups		6	8	6	8	10	6	8	10	14

4.3.2. LFE5U

Pin Information Summary		LFE5U-12			LFE5U-25			LFE5U-45				LFE5U-85			
Pin Type		256 caBGA	285 csfBGA	381 caBGA	256 caBGA	285 csfBGA	381 caBGA	256 caBGA	285 csfBGA	381 caBGA	554 caBGA	285 csfBG	381 caBGA	554 caBGA	756 caBG
General Purpose Inputs/Outputs per Bank	Bank 0	24	6	24	24	6	24	24	6	27	32	6	27	32	56
	Bank 1	32	6	32	32	6	32	32	6	33	40	6	33	40	48
	Bank 2	32	21	32	32	21	32	32	21	32	32	21	34	32	48
	Bank 3	32	28	32	32	28	32	32	28	33	48	28	33	48	64
	Bank 4	0	0	0	0	0	0	0	0	0	0	0	0	14	24
	Bank 6	32	26	32	32	26	32	32	26	33	48	26	33	48	64
	Bank 7	32	18	32	32	18	32	32	18	32	32	18	32	32	48
	Bank 8	13	13	13	13	13	13	13	13	13	13	13	13	13	13
Total Single-Ended User		197	118	197	197	118	197	197	118	203	245	118	205	259	365
VCC		6	13	20	6	13	20	6	13	20	24	13	20	24	36
VCCAUX (Core)		2	3	4	2	3	4	2	3	4	9	3	4	9	8
VCCIO	Bank 0	2	1	2	2	1	2	2	1	2	3	1	2	3	4
	Bank 1	2	1	2	2	1	2	2	1	2	3	1	2	3	4
	Bank 2	2	2	3	2	2	3	2	2	3	4	2	3	4	4
	Bank 3	2	2	3	2	2	3	2	2	3	3	2	3	3	4
	Bank 4	0	0	0	0	0	0	0	0	0	0	0	0	2	2
	Bank 6	2	2	3	2	2	3	2	2	3	4	2	3	4	4
	Bank 7	2	2	3	2	2	3	2	2	3	3	2	3	3	4
	Bank 8	1	2	2	1	2	2	1	2	2	2	2	2	2	2
TAP		4	4	4	4	4	4	4	4	4	4	4	4	4	4
Miscellaneous Dedicated		7	7	7	7	7	7	7	7	7	7	7	7	7	7
GND		27	123	99	27	123	99	27	123	99	198	123	99	198	267
NC		0	1	26	0	1	26	0	1	26	33	1	26	33	29
Reserved		0	4	6	0	4	6	0	4	6	12	4	6	12	12
Total Balls		256	285	381	256	285	381	256	285	381	554	285	381	554	756
High Speed Differential Input / Output Pairs	Bank	0	0	0	0	0	0	0	0	0	0	0	0	0	0
	Bank	0	0	0	0	0	0	0	0	0	0	0	0	0	0
	Bank	16/8	10/8	16/8	16/8	10/8	16/8	16/8	10/8	16/8	16/8	10/8	17/9	16/8	
	Bank	16/8	14/7	16/8	16/8	14/7	16/8	16/8	14/7	16/8	24/12	14/7	16/8	24/1	
	Bank	0	0	0	0	0	0	0	0	0	0	0	0	0	0
	Bank	16/8	13/6	16/8	16/8	13/6	16/8	16/8	13/6	16/8	24/12	13/6	16/8	24/1	
	Bank	16/8	8/6	16/8	16/8	8/6	16/8	16/8	8/6	16/8	16/8	8/6	16/8	16/8	
	Bank	0	0	0	0	0	0	0	0	0	0	0	0	0	0
Total High Speed		64/32	45/27	64/32	64/32	45/27	64/32	64/32	45/27	64/32	80/40	45/27	65/33	80/40	112/
DQS Groups (> 11 pins in group)	Bank	0	0	0	0	0	0	0	0	0	0	0	0	0	0
	Bank	0	0	0	0	0	0	0	0	0	0	0	0	0	0
	Bank	2	1	2	2	1	2	2	1	2	2	1	2	2	
	Bank	2	2	2	2	2	2	2	2	2	3	2	2	3	
	Bank	0	0	0	0	0	0	0	0	0	0	0	0	0	0
	Bank	2	2	2	2	2	2	2	2	2	3	2	2	3	
	Bank	2	1	2	2	1	2	2	1	2	2	1	2	2	
	Bank	0	0	0	0	0	0	0	0	0	0	0	0	0	0
Total DQS Groups		8	6	8	8	6	8	8	6	8	10	6	8	10	14